
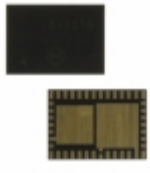
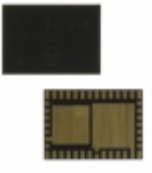




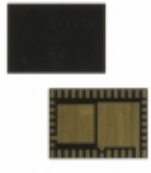

	<p>SI1013CX-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI1013CX-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 0.45A SC89-3</p> <p>Datenblätter:  SI1013CX-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 35716 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1013CX-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 0.45A SC89-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	35716 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SC-89, SOT-490
Supplier Device-Gehäuse	SC-89-3
Verlustleistung (max)	190mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	450mA (Ta)
Rds On (Max) @ Id, Vgs	760 mOhm @ 400mA, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	2.5nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	45pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)





SI1013CX-T1-GE3 ist neu im Original, Suche SI1013CX-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1013CX-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1013CX-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1013-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-WFQFN</p>	 <p>SI1013-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-WFQFN</p>	 <p>SI1013R-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 350MA SC-75A</p>	 <p>SI1013R-T1 VISHAY SI1013R-T1 VISHAY</p>
 <p>SI1013R-T1 VISHAY SI1013R-T1</p>	 <p>SI1013R-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 350MA SC-75A</p>	 <p>SI1013-C-GM2 Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 42-VFLGA</p>	 <p>SI1013C-T1 VISHAY VISHAY SOT-323</p>

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|---|---|---|--|---|
|  SI1000-C-GM |  SI1002-C-GMR |  SI1003-C-GM |  SI1011X-T1-GE3 |  SI1011X-T1-GE3 |
|  SI1012CR-T1-GE3 |  SI1012CR-T1-GE3 |  SI1012R-T1 |  SI1012R-T1-E3 |  SI1012R-T1-E3 |
|  SI1012R-T1-GE3 |  SI1012R-T1-GE3 |  SI1012X-T1 |  SI1012X-T1-E3 |  SI1012X-T1-E3 |
|  SI1012X-T1-GE3 |  SI1012X-T1-GE3 |  SI1013CX-T1-GE3 |  SI1013R-T1 |  SI1013R-T1-E3 |
|  SI1013R-T1-E3 |  SI1013R-T1-GE3 |  SI1013R-T1-GE3 |  SI1013X-T1 |  SI1013X-T1-E3 |
|  SI1013X-T1-E3 |  SI1013X-T1-GE3 |  SI1013X-T1-GE3 |  SI1016CX-T1-GE3 |  SI1016CX-T1-GE3 |
|  SI1016X-T1-E3 |  SI1016X-T1-E3 |  SI1016X-T1-GE3 |  SI1016X-T1-GE3 |  SI1016X2-T1-GE3 |
|  SI1021R-T1 |  SI1021R-T1-E3 |  SI1021R-T1-E3 |  SI1022R-T1 |  SI1022R-T1-E3 |
|  SI1022R-T1-E3 |  SI1022R-T1-GE3 |  SI1022R-T1-GE3 |  SI1022R-T1-E3 |  SI1023CX-T1-GE3 |
|  SI1023CX-T1-GE3 |  SI1023X-T1 |  SI1023X-T1-E3 |  SI1023X-T1-E3 |  SI1023X-T1-GE3 |

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